

Description

The DCSD36C is a 36V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast re-sponse time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The DCSD36C complies with the IEC 61000-4-2 (ESD) standard with ± 25 kV air and ± 20 kV contact discharge. It is assembled into an ultra-small lead-free SOD-323 package. The small size and high ESD surge protection make DCSD36C an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- ◆ 300W peak pulse power (8/20 μ s)
- ◆ Protects one data or power line
- ◆ Ultra low leakage: nA level
- ◆ Operating voltage: 36V
- ◆ Low clamping voltage
- ◆ 2-pin leadless package
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: ± 25 kV
Contact discharge: ± 20 kV
 - IEC61000-4-5 (Lightning) 4A (8/20 μ s)
- ◆ RoHS Compliant

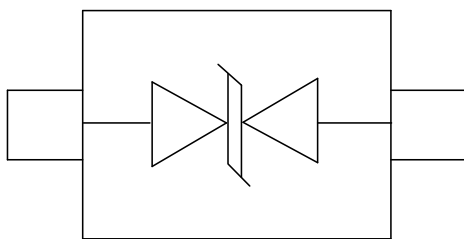
Mechanical Characteristics

- ◆ Package: SOD-323
- ◆ Case Material: "Green" Molding Compound.
- ◆ Moisture Sensitivity: Level 3 per J-STD-020
- ◆ Terminal Connections: See Diagram Below
- ◆ Marking Information: See Below

Applications

- ◆ Cellular Handsets and Accessories
- ◆ Personal Digital Assistants
- ◆ Notebooks and Handhelds
- ◆ Portable Instrumentation
- ◆ Peripherals
- ◆ Digital Cameras
- ◆ Audio Players

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information



2N=DeviceMarkingCode

Ordering Information

Part Number	Marking	Packaging	Reel Size
DCSD36C	2N	3000/Tape & Reel	7 inch

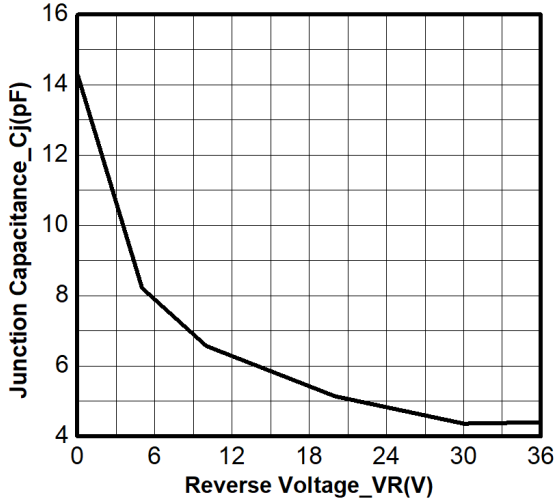
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	300	W
Peak Pulse Current (8/20 μs)	Ipp	4	A
ESD per IEC 61000-4-2 (Air)	VESD	± 25	kV
ESD per IEC 61000-4-2 (Contact)		± 20	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

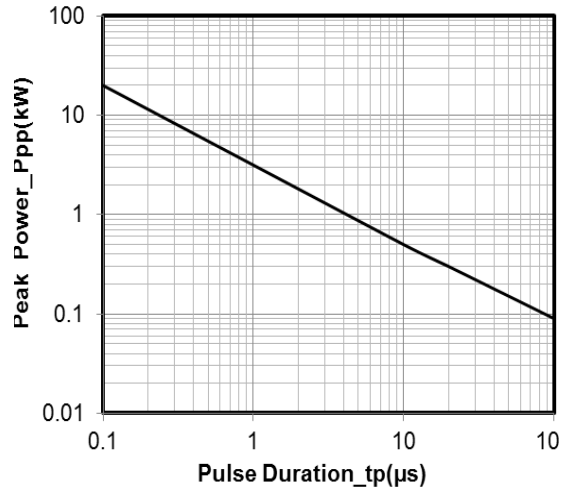
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			36	V	
Breakdown Voltage	VBR	38			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 36V
Clamping Voltage	VC			50	V	I _{PP} = 1A (8 x 20 μs pulse)
	VC			75	V	I _{PP} = 4A (8 x 20 μs pulse)
Junction Capacitance	CJ		15	20	pF	VR = 0V, f = 1MHz

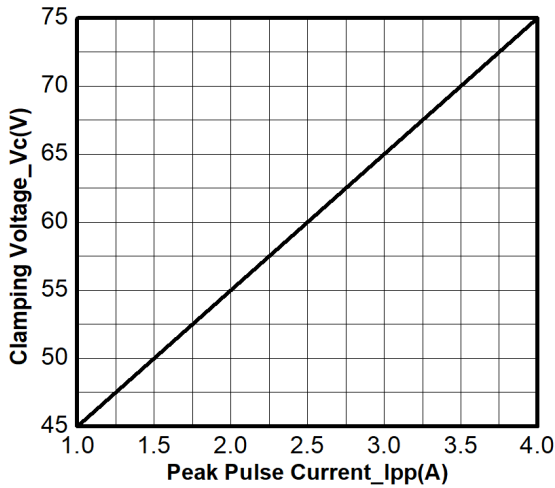
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



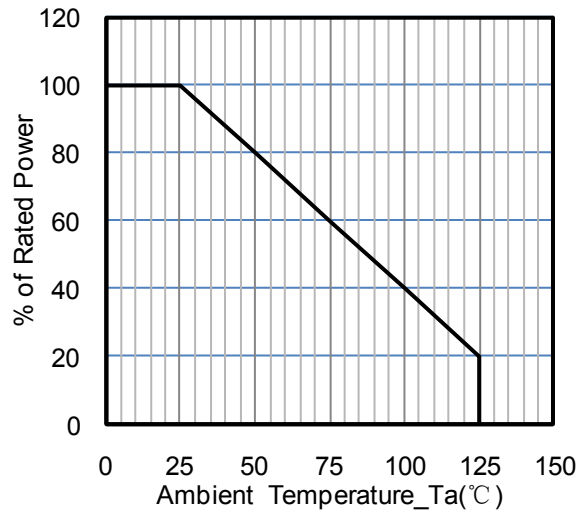
Junction Capacitance vs. Reverse Voltage



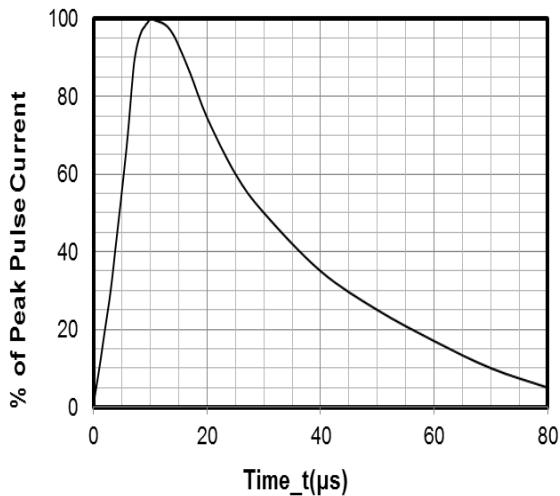
Peak Pulse Power vs. Pulse Time



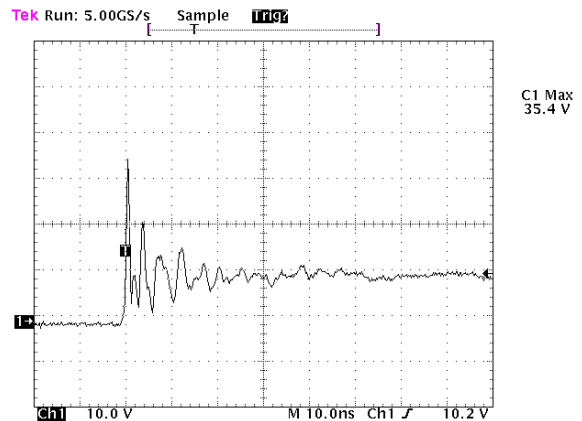
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve

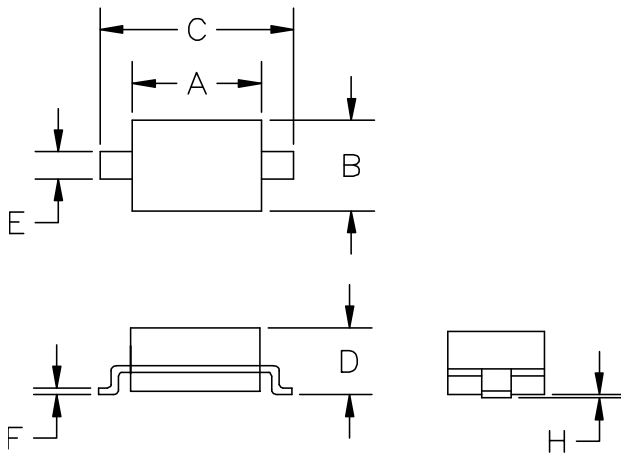


8 X 20μs Pulse Waveform



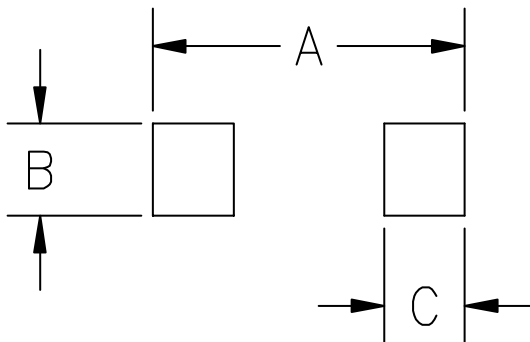
**Note: Data is taken with a 10x attenuator
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2**

SOD-323 Package Outline Drawing



SYM	DIMENSIO			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.80	0.060	0.071
B	1.20	1.40	0.045	0.054
C	2.30	2.70	0.090	0.107
D	-	1.10	-	0.043
E	0.30	0.40	0.012	0.016
F	0.10	0.25	0.004	0.010
H	-	0.10	-	0.004

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

Contact Information

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